

Micromegas detectors

- MPGD situation at the end of the nineties
- Initial Micromegas and evolutions
- Introduction of resistive layers
- Micromegas today

End of nineties, 3 main MPGD structures emerged!



It is interesting to observe that in these 3 options the amplification gaps are precisely defined by industrial materials, not by photolithography:

> -Polyimide 50um +/-0.1um -Photo-imageable coverlay spacer 128um +/-2um

1997→Micromegas (Yannis)





1998 \rightarrow GEM foil and then triple GEM detector (Fabio Sauli)







Spark problem solved by stacking 3 GEMs:

The size of the detector do not affect the performance.

A GEM is only made with Photolithographic processes. Industrial by nature.

The technology was spread rapidly.

1998→first LEM or THGEM (Pio Picchi and his team)

Mechanical Drilling : FR4, PMMA etc.. More recently: Multi electrode THGEM Sand blasting on glass Photo imaged glass







Eltos (IT) Hold by Fulvio Tessarotto



Print electronics (IS) Hold by Amos Breskin



CERN Hold by Serge Ferry



1999→Micro-Well (Ronaldo Bellazzini)



-3 x 3 cm Micro-well detector
-Produced with GEM processes
-Really simple but abandoned for a while due to the difficulty to mitigate sparks



Close-up view Square pattern used in the early days





But let's come back to MM



1997 First Micromegas (Yannis)



-Ni electroformed mesh stretched on a frame.

-Spacers done with fishing wires.

-Spark protection done with added discrete components.

-The size of the detector have an impact on the spark current.

-The Ni mesh is fragile.

-The production steps are mainly relying on manual artisanal skills .

-Challenge to produce a 30cm ×30cm detector

2000 First Evolution (Yannis) → Photo imaged pillars



-Still fragile Ni Electroformed mesh stretched on a frame.

-Spacers deposited on the PCB by photo lithographical processes.

-Still production steps relying to much on manual artisanal skills .

-Structure used initially for Compass.

-30cm × 30cm challenging

2001 Second evolution (CERN) \rightarrow Dots on mesh



KABES

-Copper Mesh done by photolithography

-Spacers are attached to the mesh and done by photolithography.

-This structure is still fragile due to the thin copper mesh .

-Structure used for KABES and CAST

-30cm x30cm challenging



Right after with similar process →Micro bulk Yannis and CERN



S Andriamonje et all 2010 JINST 5 P02001



Figure 1. Kapton pillars are created below the copper in each mesh step.

Same material as GEM (kapton + Cu) Holes created etching copper and kapton (like a GEM) Amplification in the small holes (field ~ uniform)



Figure 3. Photo of the 3.5 cm diameter circular Micromegas.



Best energy resolution among MPGD





2004 Third evolution (Yannis and CERN) \rightarrow use of stainless-steel woven mesh

BULK Micromegas



Floating mesh Micromegas



Robust mesh Repeatable industrial processes. Possibility to make large detectors of 2m × 1m The technology spread was then rapid. 7

Mesh stretching







Hot roll lamination details







Read-out board

Coverlay lamination

Mesh stretched on frame



Detector developed / cured / tested

400um pillar





Pillar matrix on 1cm x 1cm pads

BULK Micromegas detectors



T2K TPC Alain Delbart



ILC DHCAL , Max Chefdeville 1m x 1m plane With 6 detectors



Early ATLAS NSW R&D Joerg Wotschack 1.5m × 0.5m plane Single panel

CLAS 12 Cylindrical Micromegas bulk Stefan Aune



33 sectors , 12cm diameterDamien Neyret2.5mm dead space for sectorizing1mm hole for HV connection

Resistive layer introduction.
 A long path, I think not yet fully explored !



The first person who came to our workshop asking for resistive layers was again Yannis. The idea at that time was to dilute carbon powder in epoxy resin and cover read-out strips.

In 2012 during the early phase of ATLAS NSW R&D it became clear that the resistive layers are crucial.

With LHC background the single amplification stage detectors were continuously sparking, they were not damaged but simply constantly stopped due to the spark rate.

In close collaboration with <u>Joerg Wotschack</u> we dive in resistive layers.

It took us 12 iterations to find the right structure.



ATLAS NSW prototype $1m \times 2m \rightarrow Floating mesh$



Open





Closed







Atlas NSW



Joerg Wotschack



Close to 2000 Micromegas detectors produced with modules sizes up to $2m \times 0.5m$

PCBs with pillars built at ELTOS (IT) and ELVIA (FR)

Meshes stretched and glued on frame in Thessaloniki

Honey-comb panels construction and detector Assembly : -Dubna -INFN Frascati -CEA Saclay (Fabien Jeanneau's gang) -LMU Munich MPT participated to the R&D and was also involved in the mass production with industry -Specification -Companies selection -Technology transfer

Right after we did a Survey on existing resistive layers to take a direction for the future

Polymer paste 10Kohms to 100K/Square

RuO Thick film paste 10K to 100M/square

Resistive ceramics or glass

Resistive Kapton

Dissipative films

DLC: Diamond Like Carbon

Too low values (but strips can artificially increase the value)

Perfect range , but the substrate must be ceramic

Limitation on resistive values and size

Limitation on resistive values

Too high values

Perfect range 100K to $1T \rightarrow$ chosen direction

First benefit coming from resistive layers : Spark protection

No structural defect No process above 100deg No effect on metals or Polymers

- Spark energy : $\frac{1}{2}$ CV2
 - 600 uJ in a 10cm x 10cm GEM. ←
 - 30 uJ with a classical MM 10cm x10cm.
 - 0.06 uJ with a 10M resistive layer.
- Below 10M/square.
 - We can still create some visible compounds.
 - There is still enough energy to slightly deteriorate dielectrics.
- Above 10M/square
 - No visible compounds.
 - The structure is never damage.
 - But low Humidity and High cleanliness are mandatory !



Massive structural effects Metal melting Kapton evaporation Processes happening above 1000 deg But thanks to Triple GEM structure

But thanks to Triple GEM struct this is not happening

second benefit : Resistive spreading

spice simulation Virginia university collaboration



Pulse amplitude and time shift with a 1MOhms/SQR layer

1600 cells 0.125mm x 0.125mm

Resistive spreading







Classical MM C4 is defining the Spark current C4 is in the range of 300pF

Resistive MM C3 is defining the Spark current and C3 is less than 1pF

$2013-2023 \rightarrow MM$ with resistive layers



$2016 \rightarrow PicoSec$ precise timing with Micromegas



Schematic not drawn to scale

X. Wang et al., Study of DLC photocathode for PICOSEC detector, RD51 collaboration meeting, October 2018

PicoSec detector modules







Single pad (2016) Pads ø1 cm **Multi pad (2017)** Pads ◯ 1 cm **10x10 module (2022)** Pads □ 1 cm

Conclusion

Yannis have triggered nearly all the major MM improvements

There is now a solution for nearly all applications:

large size, shape, protection , rate , space resolution, mass production , time resolution etc.

Yannis could you help us to face our last problem :

Improving the robustness of photocathode layers for precise timing detectors



C1: capacity mesh to GNDmany nFC2: strip capacity to GNDin the range of 20 pFC3: strip capacity to meshin the range of 10pfC4: spark protection capacitorin the range of 300pF \rightarrow 10 x (C2//C3)R1: polarization resistor1MR2: peak spark current limitation20 Ohms to protect the external diodes



C1 : capacity mesh to GND

- C2 : strip capacity to GND
- C3 : strip capacity to mesh
- C4 : spark protection capacitor
- R1 : polarization resistor
- R2 : peak spark current limitation

many nF in the range of 20 pF in the range of 10pf in the range of $300pF \rightarrow 10 \times (C2//C3)$ 1M

20 Ohms to protect the external diodes

The spark current is defined by C4 serial to R2 through outer diodes. This spark current do not flow through the amplifier. Without external diodes the inner diodes would have been damaged. Without C4, C1 defines a so large current that the outer diodes would have been damaged, melting also the mesh.



| C1 : capacity mesh to GND | many nF |
|--|--------------------------------------|
| C2 : strip capacity to GND | in the range of 20 pF |
| C3 : local capacity res layer to mesh | below the pF |
| C4 : local capacity res layer to strip | below the pF |
| R1 : embedded resistor | part of the resistive strip or layer |



C1 : capacity mesh to GND many nF C2 : strip capacity to GND in the range of 20 pF amplifier internal diodes. C3 : local capacity res layer to mesh below the pF C4 : local capacity res layer to strip below the pF External diodes are not necessary. R1 : embedded resistor part of the resistive strip or layer

The peak spark current flowing in the amplifier is defined by C3 and the Approximately 1000 time less the previous scheme.